JOURNALOF

Ceramic Processing Research

Corrosion and oxidation behavior of $ASiO_4$ (A=Ti, Zr and Hf) and silicon nitride with an HfSiO₄ environmental barrier coating

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The oxidation and water vapor corrosion behavior of sintered $HfSiO_4$, $ZrSiO_4$, $TiSiO_4$ compacts and high density $HfSiO_4$ coated silicon nitride ceramics were examined at 1500 °C in a static state water vapor environment. The bulk weights of $HfSiO_4$ and $ZrSiO_4$ decreased after the water vapor corrosion test with a weight loss rate of 7.080×10^{-6} and 1.333×10^{-6} g/cm²·h, respectively. The weight of $TiSiO_4$ remained unchanged within the experimental error after the corrosion test. A trace of corrosion was observed on the surface of grains of corrosion-tested compacts. On the other hand, the weight of high density $HfSiO_4$ layer (Environmental Barrier Coating, EBC layer) coated silicon nitride specimens increased with a weight gain rate 1.495×10^{-6} g/cm²·h, which is attributed by the oxidation of the silicon nitride substrate.

Key words: Water vapor corrosion, oxidation, HfSiO₄, ZrSiO₄, TiSiO₄, silicon nitride.

Introduction

Silicon nitride ceramics are excellent candidates as gas turbine materials because of their high thermal and mechanical properties at elevated temperatures [1, 2]. However, silicon nitride ceramics are easily oxidized and corroded at high temperatures in water vapor environments such as in gas combustion fields [3, 4]. Hence, protective environmental barrier coating (EBC) layers are necessary for the application of silicon nitride ceramics in gas turbine components. It has been suggested that the recession of silicon nitride ceramics by water vapor and/or combustion gas is caused by a combination of oxidation/corrosion of silicon nitride ceramic substrates and corrosion of the silica that is formed on silicon nitride ceramic substrates, where the silica component is volatile.

The selection of an EBC material is critical, as many parameters have to be considered. For example, as the EBC layer is coated directly on the silicon nitride substrate, the thermal expansion coefficients (TEC) of EBC materials must be close to that of silicon nitride. Therefore, silicates which have low TECs are desirable for the EBC layer. Among the low thermal expansion silicate compounds, $Ln_2Si_2O_7$ (Ln=rare earth element) and $ASiO_4$ (A is IV group elements, Ti, Zr, Hf) are potential as EBC materials because of their thermal stability and in particular Yb₂Si₂O₇ and HfSiO₄ are most preferable materials because their TECs are almost the same as that of silicon nitride ceramics.

In our previously published papers, we reported that the corrosion rate of $Yb_2Si_2O_7$ is on the order of 10^{-4} g/ cm²·h during a static state water vapor corrosion test, which is higher than that of Lu₂Si₂O₇ [5] and subsequently, the oxidation rate of silicon nitride with an $Yb_2Si_2O_7$ EBC is larger than that of silicon nitride with a Lu₂Si₂O₇ EBC layer [6].

In the present work, corrosion tests for $HfSiO_4$, $ZrSiO_4$, $TiSiO_4$ and high density $HfSiO_4$ EBC layer coated silicon nitride were performed at 1500 °C in a static state water vapor environment. The corrosion and/or oxidation mechanism for these materials are discussed.

Experimental

For the preparation of bulk silicates, high purity TiO_2 , ZrO_2 , HfO_2 and SiO_2 powders were used as the starting materials. A stoichiometric molar ratio of these powders for the respective system were mixed in an agate mortar and pressed into pellets. The sintering of these pellets was performed at 1500 °C for 24 hours in air.

Oxidation bonded by a reaction sintering method [7] was employed to coat the $HfSiO_4$ EBC layer on to silicon nitride. SN-282 (Kyocera Co. Ltd.) silicon nitride ceramic was used as the substrate. By the oxidation of silicon nitride ceramic at 1000 °C, a thin amorphous silica layer was formed on the surface. To coat the $HfSiO_4$ layer on to the silicon nitride, the silicon nitride substrate with a thin layer of SiO₂ was

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kept inside an HfO_2 powder bed and sintered at 1500 °C for 4 hours in an argon atmosphere (0.5 MPa).

A high temperature water vapor corrosion test was performed using a Corrosion Testing Machine (Japan Ultra-high Temperature Materials Research Center). The samples were placed on a high purity HfO₂ jig and then heated with the following conditions; Temperature: 1500 °C, Time: 50 hours, Gas flow: 30 wt% water (air:H₂O=70:30 (wt%)), gas flow rate: 175 ml/min which corresponds to 4.6×10^{-4} m/s in velocity. To exclude any water vapor corrosion occurring at low temperatures, the corrosive gas was introduced when the temperature reached 1500 °C and the gas flow was stopped after the 50 hours testing period.

Results and Discussion

The bulk weight of silicates decreased during the corrosion test. The weight loss rates of $TiSiO_4$ and $ZrSiO_4$ were estimated as 7.080×10^{-6} and 1.333×10^{-6} g/cm²·h, respectively. The weight of $TiSiO_4$ was



Fig. 1. SEM images of $TiSiO_4$, $ZrSiO_4$ and $HfSiO_4$ samples surface after the test.

unchanged within experimental error during the test. In terms of weight changes, the corrosion resistance of $ASiO_4$ (A=Ti, Zr and Hf) decreases with an increase in atomic number of A.

Figures 1(a), (b) and (c) show the TiSiO₄, ZrSiO₄ and HfSiO₄ sample surfaces after the test, respectively. In the case of HfSiO₄, it can be seen that fine grains were deposited on the surface. Figures 2 show magnified SEM images of Fig. 1. Fine etch pits can be observed on the grain surfaces for all samples. These etch pits can be considered as a trace of the corrosion. The TiSiO₄ phase was also corroded even though its weight was unchanged during the test. The size of the pits on the HfSiO₄ sample is larger than those on TiSiO₄ and ZrSiO₄. Figure 3 shows an X-ray diffraction pattern of the HfSiO₄ sample surface after the corrosion test. HfO₂ peaks can be observed. Thus, the deposited grains shown Figs. 2(c) can be considered to be the HfO₂ phase.

From the results above, it is confirmed that the water vapor corrosion of ASiO₄ occurs at the grain surfaces



Fig. 2. Magnified SEM images of Figs. 1.



Fig. 3. X-ray diffraction pattern of HfSiO_4 sample surface after the test.

and the surface decomposes into AO₂. As is well known the silica phase is easily corroded by water vapor at high temperatures [3], the corrosion of these phases occurs according to equation (1).

$$ASiO_4(s) + 2H_2O(g) = AO_2(s) + Si(OH)_4(g)$$
 (1)

The weight loss rates of these samples are of same order of magnitude as that of the $Lu_2Si_2O_7$ phase reported previously [5]. Thus, these materials are ideal candidates for EBC materials. However, the TEC of ZrSiO₄ is slightly larger than that of silicon nitride ceramic. Among these materials, the TEC of HfSiO₄ is



Fig. 4. SEM images of the surface and the cross section of EBC coated sample.



Fig. 5. SEM images of the sample surface after the test.

almost the same as that of silicon nitride. Therefore, an $HfSiO_4$ EBC layer was coated on a silicon nitride substrate by the method mentioned above. Figures 4(a) and (b) show the surface and cross sectional images of an EBC coated silicon nitride sample before the corrosion test. The surface is covered with whisker-like $HfSiO_4$ crystalline phase.

The weight of this sample increased during the corrosion test with weight gain rate of 1.495×10^{-6} g/ cm²·h. It is considered that the weight gain was caused by the oxidation of the silicon nitride substrate. However, the weight gain rate for the HfSiO₄ EBC sample is smaller than that of the ZrSiO₄ sample which was 2.298×10^{-6} g/cm²·h [6] that was examined under same experimental conditions, namely, in the case of the HfSiO₄ EBC sample, the oxidation of the substrate was better restrained than with the ZrSiO₄ EBC sample in our previous report [6]. Figures 5(a) and (b) show SEM images of the sample surface after the test. Many cracks were induced during the test. Many etch pits can be observed on the EBC surface as shown in the magnified SEM image (b). The etch pit morphology generated is the same as in Figs. 2(c). Thus the weight gain of this sample during the test includes the weight loss by the water vapor corrosion and the weight gain by the oxidation of the substrate.

In the case of the $ZrSiO_4$ EBC sample, many cracks were induced by the corrosion test [6] the same as in this study. Figures 6(a) and (b) show segmented images



Fig. 6. Segmented images of cracks for $HfSiO_4$ and $ZrSiO_4$ EBC samples in the same range.

of cracks for HfSiO₄ and ZrSiO₄ EBC samples at the same magnification. Apparently, the length of cracks for the ZrSiO₄ EBC sample is longer than that for the HfSiO₄ EBC sample. The TEC of SN-282 silicon nitride ceramics is 3.54×10^{-6} /K [8]. On the other hand, the TECs of ZrSiO₄ and HfSiO₄ are 4.43×10^{-6} /

K and 3.6×10^{-6} /K, respectively. Because the TEC difference between the EBC layer and the substrate for the HfSiO₄ EBC sample is smaller than that for the ZrSiO₄ EBC sample, it is considered that the crack length per unit area of the HfSiO₄ EBC sample is shorter than that for the ZrSiO₄ EBC sample.

Conclusions

ASiO₄ phases were corroded in a water vapor environment with a weight loss rate less than 10^{-6} g/ cm²·h and many fine etch pits were generated on the grain surfaces. The corrosion rate of the HfSiO₄ sample was larger than that of the ZrSiO₄ and TiSiO₄ samples, however, the oxidation of the silicon nitride substrate was better restrained by the HfSiO₄ EBC. Cracks were induced during the corrosion test and the crack length for the HfSiO₄ EBC sample was shorter than that for the ZrSiO₄ EBC sample.

References

- S.M. Wiederhon, and M.K. Ferber, Current Opinion in Solid State and Materials Science 5 (2001) 311-316.
- H.J. Choi, J.G. Lee, and Y.W. Kim, J. Mater. Sci. 32 (1997) 1937-1942.
- 3. E.J. Opila, J. Am. Ceram. Soc. 86 (2003) 1238-48.
- D.S. Fox, E.J. Opila, Q.N. Nguyen, D.L. Humphrey, and S.M. Lewton, J. Am. Ceram. Soc. 86 (2003) 1256-61.
- 5. S. Ueno, N. Kondo, D.D. Jayaseelan, T. Ohji, and S. Kanzaki, ASME Paper 2003 GT2003-38878.
- S. Ueno, D.D. Jayaseelan, and T. Ohji, J. Ceramic Processing Research in press.
- 7. S. Ueno, D.D. Jayaseelan, and T. Ohji, Int. J. Appl. Ceram. Technol. in press.
- T. Fukudome, S. Tsuruzono, W. Karasawa, and Y. Ichikawa, ASME Paper 2002 GT2002-30627.